Elektronische Bauelemente

2SC2216

0.05 A , 50 V

NPN Plastic Encapsulated Transistor

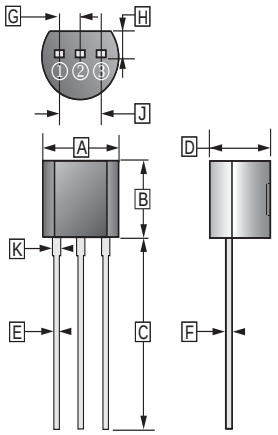
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

FEATURES

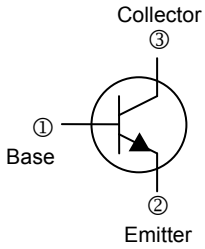
- Amplifier dissipation NPN Silicon

TO-92



①Base
②Emitter
③Collector

REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	4	V
Collector Current - Continuous	I_C	50	mA
Collector Power Dissipation	P_C	300	mW
Junction, Storage Temperature	T_J, T_{STG}	125, -55~125	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	50	-	-	V	I_C=100μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	45	-	-	V	I_C=10mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	4	-	-	V	I_E=100μA, I_C=0
Collector Cut – Off Current	I_{CBO}	-	-	0.1	μA	V_{CB}=50V, I_E=0
Emitter Cut – Off Current	I_{EBO}	-	-	0.1	μA	V_{EB}=3V, I_C=0
DC Current Gain	h_{FE}	40	-	140		V_{CE}=12.5V, I_C=12.5mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.2	V	I_C=15mA, I_B=1.5mA
Base to Emitter voltage	$V_{BE(sat)}$	-	-	1.5	V	I_C=15mA, I_B=1.5mA
Transition Frequency	f_T	300	-	-	MHz	V_{CE}=12.5V, I_C=12.5mA
Collector Output Capacitance	C_{ob}	-	-	2	pF	V_{CB}=10V, I_E=0, f=30MHz

CHARACTERISTIC CURVES